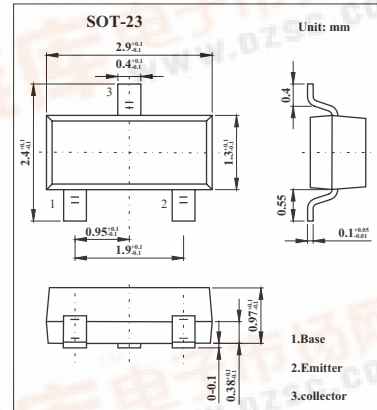


SMD Type Transistors

NPN General Purpose Amplifier  
BSS64

■ Features

- NPN general purpose amplifier



■ Absolute Maximum Ratings Ta = 25°C unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V <sub>CE0</sub>	80	V
Collector-base voltage	V <sub>CB0</sub>	120	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	200	mA
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C
Total device dissipation	P <sub>D</sub>	350	mW
Derate above 25°C		2.8	mW/°C
Thermal resistance, junction to ambient	R <sub>θJA</sub>	357	°C/W

■ Electrical Characteristics Ta = 25°C unless otherwise noted

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = 4.0 mA, I <sub>B</sub> = 0	80			V
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = 100 μA, I <sub>E</sub> = 0	120			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100 μA, I <sub>c</sub> = 0	5			V
Collector-cutoff current	I <sub>cBO</sub>	V <sub>CB</sub> = 90 V, I <sub>E</sub> = 0			0.1	μA
		V <sub>CB</sub> = 90 V, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C			50	μA
Emitter-base cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5.0 V, I <sub>c</sub> = 0			200	nA
DC current gain	h <sub>FE</sub>	I <sub>c</sub> = 10 mA, V <sub>CE</sub> = 1.0 V	20			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 4.0 mA, I <sub>B</sub> = 400μA			0.15	V
		I <sub>c</sub> = 50 mA, I <sub>B</sub> = 15 mA			0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = 4.0 mA, I <sub>B</sub> = 400 μA			1.2	V
Current gain - bandwidth product	f <sub>T</sub>	I <sub>c</sub> = 4.0 mA, V <sub>CE</sub> = 10, f = 35 MHz	60			MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, f = 1.0 MHz			5	pF

■ Marking

Marking	U3
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